



AO8403

P-Channel Enhancement Mode Field Effect Transistor

General Description

The AO8403 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.

Features

- V_{DS} (V) = -20V
- I_D = -4 A
- $R_{DS(ON)} < 42m\Omega$ ($V_{GS} = -4.5V$)
- $R_{DS(ON)} < 52m\Omega$ ($V_{GS} = -2.5V$)
- $R_{DS(ON)} < 70m\Omega$ ($V_{GS} = -1.8V$)
- ESD Rating: 3000V HBM



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current ^A	$T_A=25^\circ C$ $T_A=70^\circ C$	-4	A
		I_D	
Pulsed Drain Current ^B	I_{DM}	-30	
Power Dissipation ^A	$T_A=25^\circ C$ $T_A=70^\circ C$	1.5	W
		P_D	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	64	83	$^\circ C/W$
Maximum Junction-to-Ambient ^A		Steady-State	89	
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	53	70	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-16\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 4.5\text{V}$ $V_{DS}=0\text{V}$, $V_{GS}=\pm 8\text{V}$			± 1 ± 10	μA μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-0.3	-0.55	-1	
$I_{D(ON)}$	On state drain current	$V_{GS}=-4.5\text{V}$, $V_{DS}=-5\text{V}$	-25			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-4.5\text{V}$, $I_D=-4\text{A}$ $T_J=125^\circ\text{C}$ $V_{GS}=-2.5\text{V}$, $I_D=-4\text{A}$ $V_{GS}=-1.8\text{V}$, $I_D=-3\text{A}$		35 48 45 56	42 60 52 70	$\text{m}\Omega$ $\text{m}\Omega$ $\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-4\text{A}$	8	16		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$		-0.78	-1	V
I_S	Maximum Body-Diode Continuous Current				-2.2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance			1450		pF
C_{oss}	Output Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=-10\text{V}$, $f=1\text{MHz}$		205		pF
C_{rss}	Reverse Transfer Capacitance			160		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		6.5		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge			17.2		nC
Q_{gs}	Gate Source Charge	$V_{GS}=-4.5\text{V}$, $V_{DS}=-10\text{V}$, $I_D=-4\text{A}$		1.3		nC
Q_{gd}	Gate Drain Charge			4.5		nC
$t_{D(on)}$	Turn-On DelayTime			9.5		ns
t_r	Turn-On Rise Time	$V_{GS}=-4.5\text{V}$, $V_{DS}=-10\text{V}$, $R_L=2.5\Omega$, $R_{GEN}=3\Omega$		17		ns
$t_{D(off)}$	Turn-Off DelayTime			94		ns
t_f	Turn-Off Fall Time			35		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-4\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		31		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-4\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		13.8		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any a given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.